

2013 Twentieth International Workshop on Active-Matrix Flatpanel Displays and Devices

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H. Hamada, *Kinki Univ., Japan*

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This workshop is moderated by:

A. Heya (*Univ. of Hyogo*)
T. Matsuda (*Ryukoku Univ.*)
H. Okada (*Univ. of Toyama*)
T. Toyama (*Osaka Univ.*)
N. Watanabe (*Sharp*)